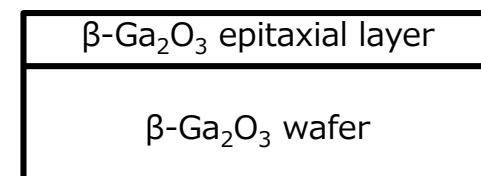


Standard specifications of 25x25mm² MBE β -Ga₂O₃ epitaxial wafers

Epitaxial layer (Growth method: MBE)

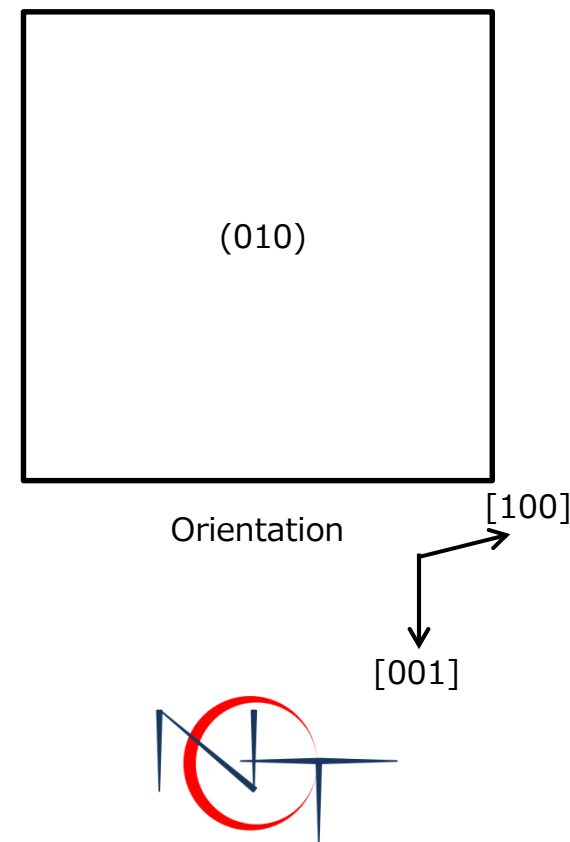
Property	Specification	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration	Specify a value in the range between 1×10^{17} and $2 \times 10^{18} \text{ cm}^{-3}$	-
Thickness	Specify a value in the range between 0.1 and 0.5 μm	



Cross section of β -Ga₂O₃ epitaxial wafers

Wafers

Property	Specification
Dopant	Fe (semi-insulating)
Doping concentration	-
Resistivity	$> 10^{10} \Omega\text{cm}$
Orientation	(010)
Size	25x25 mm ²
Thickness	0.5 mm
XRD FWHM	$\leq 350 \text{ arcsec}$
Off set angle	$0^\circ \pm 1^\circ$



Remarks

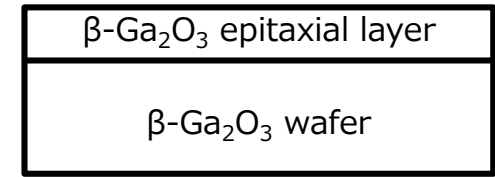
- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.

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Standard specifications of 10x15mm² MBE β -Ga₂O₃ epitaxial wafers

Epitaxial layer (Growth method: MBE)

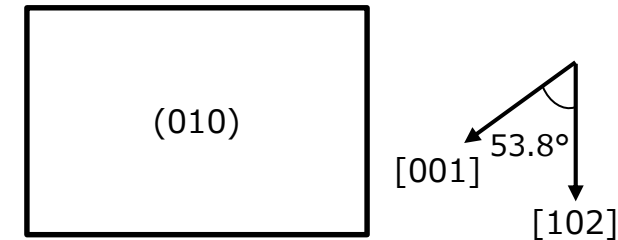
Property	Specification	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration	Specify a value in the range between 1×10^{17} and $2 \times 10^{18} \text{ cm}^{-3}$	-
Thickness	Specify a value in the range between 0.1 and 0.5 μm	



Cross section of β -Ga₂O₃ epitaxial wafers

Wafers

Property	Specification	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration	$1-9 \times 10^{18} \text{ cm}^{-3}$	-
Resistivity	-	$> 10^{10} \Omega\text{cm}$
Orientation	(010)	
Size	10x15 mm ²	
Thickness	0.5 mm	
XRD FWHM	$\leq 150 \text{ arcsec}$	
Off set angle	$0^\circ \pm 1^\circ$	



Orientation



Novel Crystal Technology, Inc.

Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.